



M.S.KENNEDY CORP.

75 VOLT 20 AMP MOSFET H-BRIDGE PWM MOTOR DRIVER/AMPLIFIER

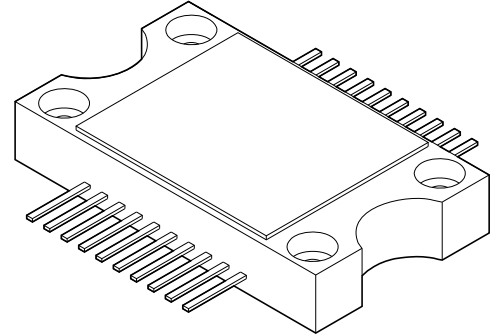
4225

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FEATURES:

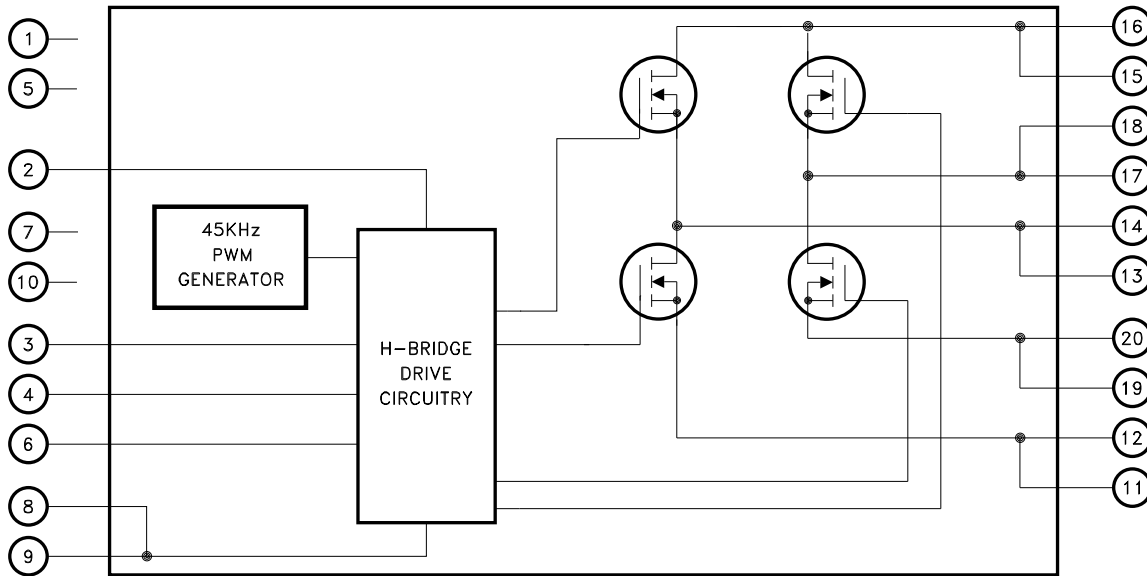
- Low RDS(ON) 0.013Ω Typical
- Low Cost, Non-Hermetic, Complete H-Bridge
- 20 Amp Capability, 75 Volt Maximum Rating
- Self-contained Smart Lowside/Highside Drive Circuitry
- Internal 45KHz PWM Generation, Shoot-through Protection
- Isolated Case Allows Direct Heatsinking
- Logic Level Disable Input
- Logic Level High Side Enable Input for Special Modulation or Function



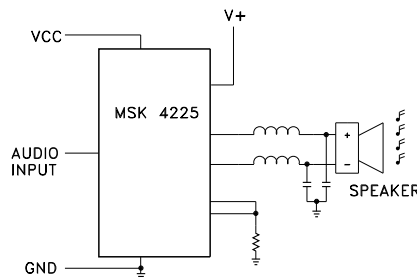
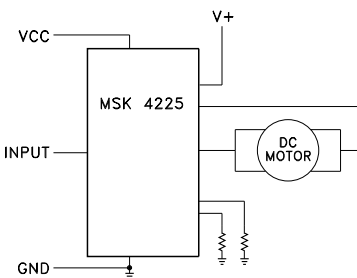
DESCRIPTION:

The MSK 4225 is a complete H-Bridge circuit to be used for DC brushed motor control or Class D switchmode amplification. All of the drive/control circuitry for the lowside and highside switches are internal to the circuit. The 45KHz PWM circuitry is internal as well, leaving the user to only provide an analog signal for the motor speed/direction, or audio signal for switchmode audio amplification. The MSK 4225 is constructed in a space efficient plastic power package that can be directly bolted to a heatsink.

EQUIVALENT SCHEMATIC



TYPICAL APPLICATIONS



PIN-OUT INFORMATION

1	NC	20	RSENSE A
2	VCC	19	RSENSE A
3	HEN	18	OUTPUT A
4	DIS	17	OUTPUT A
5	NC	16	V+
6	INPUT	15	V+
7	NC	14	OUTPUT B
8	GND	13	OUTPUT B
9	GND	12	RSENSE B
10	NC	11	RSENSE B

ABSOLUTE MAXIMUM RATINGS ^⑤

V+	High Voltage Supply ^⑥	75V	T _{ST}	Storage Temperature Range	-55°C to +125°C
VCC	Logic Supply	16V	T _{LD}	Lead Temperature Range	300°C (10 Seconds)
I _{OUT}	Continuous Output Current	20A	T _C	Case Operating Temperature	MSK4225
I _{PK}	Peak Output Current	40A			-40°C to +85°C
V _{OUT}	Output Voltage Range	GND -2V min. to V+ max.	T _J	Junction Temperature	+150°C
θ _{JC}	Thermal Resistance	3.0°C/W			(Output Switches @ 125°C)

ELECTRICAL SPECIFICATIONS

T_C = +25°C Unless Otherwise Specified

Parameter	Test Conditions ^②	MSK 4225			Units
		Min.	Typ.	Max.	
OUTPUT CHARACTERISTICS					
R _{DS} (ON) ^{① ④}	Each MOSFET I _D = 20A	-	-	0.013	Ω
V _{DS} (ON) Voltage	Each MOSFET I _D = 20A ^③	-	0.45	0.52	V
Instantaneous Forward Voltage	Each MOSFET I _S = 20A Intrinsic Diode ^③	-	1.0	1.3	V
Reverse Recovery Time ^①	Intrinsic Diode	-	-	280	nS
Leakage Current	Each MOSFET V ₊ = 70V	-	10	250	uA
PWM Frequency		40	45	50	KHz
VCC SUPPLY CHARACTERISTICS					
Quiescent Bias Current	Analog Input = 6Vdc	-	43	50	mA
VCC Voltage Range ^①		10	12	15	V
INPUT SIGNAL CHARACTERISTICS ^①					
Analog Input Voltage	Output A,B = 50% Duty Cycle	-	6	-	V
Analog Input Voltage	Output A = 100% Duty Cycle High	-	9	-	V
Analog Input Voltage	Output B = 100% Duty Cycle High	-	3	-	V
LOGIC CONTROL INPUTS ^①					
Disable Input	Input Voltage LO	-	-	0.8	V
	Input Voltage HI	2.7	-	-	V
	Input Current (DISABLE = 0V)	-	-	135	uA
HEN Input	Input Voltage LO	-	-	0.8	V
	Input Voltage HI	2.7	-	-	V
	Input Current (HEN = 0V)	-	-	270	uA
SWITCHING CHARACTERISTICS ^①					
	R _L = 100Ω				
Rise Time		-	40	-	nS
Fall Time		-	30	-	nS
Dead Time		-	45	-	nS

NOTES:

- ① Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
- ② VCC = +12V, V+ = 28V, RSENSE A,B = Ground, DIS = 0V, HEN = N/C unless otherwise specified.
- ③ Measured using a 300μS pulse with a 2% Duty Cycle.
- ④ On Resistance is specified for the Internal MOSFET for Thermal Calculations. It does not include the package pin resistance.
- ⑤ Continuous operation at or above absolute maximum ratings may adversely effect the device performance and/or life cycle.
- ⑥ When applying power to the device, apply the low voltage followed by the high voltage or alternatively, apply both at the same time. Do not apply high voltage without low voltage present.

TYPICAL PERFORMANCE CURVES

